

CLAIMS

What is claimed:

1. A method of fabricating a semiconductor device, having a copper-zinc alloy (Cu-Zn) thin film formed on a copper (Cu) surface by electroplating the Cu surface in a chemical solution, comprising the steps of:
5 providing a semiconductor substrate having a Cu surface;
providing a chemical solution;
electroplating the Cu surface in the chemical solution, thereby forming a Cu-Zn
alloy thin film on the Cu surface;
rinsing the Cu-Zn alloy thin film in a solvent;
drying the Cu-Zn alloy thin film under a gaseous flow; and
completing formation of the semiconductor device.

10 2. A method, as recited in Claim 1,
wherein the chemical solution is nontoxic and aqueous, and
wherein the chemical solution comprises:
5 at least one zinc (Zn) ion source for providing a plurality of Zn ions;
at least one copper (Cu) ion source for providing a plurality of Cu ions;
at least one complexing agent for complexing the plurality of Cu ions;
at least one pH adjuster; and
at least one wetting agent for stabilizing the chemical solution, all being
dissolved in a volume of deionized (DI) water.

5 3. A method, as recited in Claim 1,
wherein the at least one zinc (Zn) ion source comprises at least one zinc salt
selected from a group consisting essentially of zinc acetate ((CH₃CO₂)₂Zn),
zinc bromide (ZnBr₂), zinc carbonate hydroxide (ZnCO₃·2Zn(OH)₂), zinc
dichloride (ZnCl₂), zinc citrate ((O₂CCH₂C(OH)(CO₂)CH₂CO₂)₂Zn₃), zinc
iodide (ZnI₂), zinc L-lactate ((CH₃CH(OH)CO₂)₂Zn), zinc nitrate
(Zn(NO₃)₂), zinc stearate ((CH₃(CH₂)₁₆CO₂)₂Zn), zinc sulfate (ZnSO₄), zinc
sulfide (ZnS), zinc sulfite (ZnSO₃), and their hydrates.

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4. A method, as recited in Claim 1,
wherein the chemical solution further comprises at least one complexing agent for
complexing the plurality of Zn ions being dissolved in the volume of DI
water,

5. wherein the at least one complexing agent for complexing the plurality of Zn ions
comprises tartaric acid ($\text{HO}_2\text{CCH}(\text{OH})\text{CH}(\text{OH})\text{CO}_2\text{H}$), and
wherein the tartaric acid prevents precipitation of the plurality of Zn ions from the
chemical solution.

5. A method, as recited in Claim 1,
wherein the at least one copper (Cu) ion source comprises at least one copper salt
selected from a group consisting essentially of copper(I) acetate
($\text{CH}_3\text{CO}_2\text{Cu}$), copper(II) acetate ((CH_3CO_2)₂Cu), copper(I) bromide (CuBr),
copper(II) bromide (CuBr₂), copper(II) hydroxide (Cu(OH)₂), copper(II)
hydroxide phosphate (Cu₂(OH)PO₄), copper(I) iodide (CuI), copper(II)
nitrate hydrate ((CuNO₃)₂), copper(II) sulfate (CuSO₄), copper(I) sulfide
(Cu₂S), copper(II) sulfide (CuS), copper(II) tartrate ((CH(OH)CO₂)₂Cu), and
their hydrates.

6. A method, as recited in Claim 1,
wherein the at least one complexing agent for the plurality of Cu ions comprises at
least one species selected from a group consisting essentially of ethylene
diamine “EDA” (H₂NCH₂CH₂NH₂) and ethylenediaminetetraacetic acid
“EDTA” ((HO_2CCH_2)₂NCH₂CH₂N(CH₂CO₂H)₂), and
wherein the at least one complexing agent for the plurality of Cu ions prevents
precipitation of the plurality of Cu ions from the chemical solution.

7. A method, as recited in Claim 1,
wherein the at least one pH adjuster comprises at least one pH-adjusting compound
selected from a group consisting essentially of ammonium hydroxide
(NH₄OH) and tetramethylammonium hydroxide “TMAH” ((CH₃)₄NOH).

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8. A method, as recited in Claim 1,
wherein the at least one wetting agent comprises a surfactant, and
wherein the surfactant comprises at least one material selected from a group
consisting essentially of RE-610™ and polyethylene glycol (PEG).

9. A method, as recited in Claim 1,
wherein the Cu surface is formed by a process selected from a group consisting
essentially of chemical vapor deposition (CVD), plasma vapor deposition
(PVD), plasma enhanced chemical vapor deposition (PECVD),
electroplating, and electroless plating,
wherein said solvent comprises water, and
wherein said gaseous flow comprises gaseous nitrogen (GN₂).

10. A method, as recited in Claim 1,
wherein the at least one zinc (Zn) ion source is provided in a concentration range of
approximately 5 g/L to approximately 25 g/L,
wherein the at least one complexing agent for complexing the plurality of Zn ions is
provided in a concentration range of approximately 10 g/L to approximately
30 g/L,
wherein the at least one copper (Cu) ion source is provided in a concentration range
of approximately 5 g/L to approximately 25 g/L,
wherein the at least one complexing agent for complexing the plurality of Cu ions is
provided in a concentration range of approximately 40 g/L to approximately
100 g/L,
wherein the at least one pH adjuster is provided in a concentration range of
approximately 10 g/L to approximately 20 g/L,
wherein the at least one wetting agent is provided in a concentration range of
approximately 0.01 g/L to approximately 0.1 g/L, and
wherein the volume of water is provided in a volume range of up to and including
1 L,
wherein the at least one pH adjuster adjusts the chemical solution to a pH in a range
of approximately 7.5 to approximately 14,

wherein the chemical solution is maintained at a temperature in a range of approximately 16°C to approximately 35°C,

wherein the Cu surface is immersed for a time duration in a range of approximately 15 seconds to approximately 120 seconds,

wherein the Cu-Zn alloy thin film is formed having a thickness in a range of approximately 10 nm to approximately 200 nm, and

wherein the formed Cu-Zn alloy thin film is Zn content in a concentration range of approximately 0.10 atomic % to 1 atomic %.

11. A semiconductor device, having a copper-zinc alloy (Cu-Zn) thin film formed on a copper (Cu) surface by electroplating the Cu surface in a chemical solution, fabricated by a method comprising the steps of:
 - providing a semiconductor substrate having a Cu surface;
 - providing a chemical solution;
 - electroplating the Cu surface in the chemical solution, thereby forming a Cu-Zn alloy thin film on the Cu surface;
 - rinsing the Cu-Zn alloy thin film in a solvent;
 - drying the Cu-Zn alloy thin film under a gaseous flow; and
 - completing formation of the semiconductor device.
12. A device, as recited in Claim 11,
wherein the chemical solution is nontoxic and aqueous, and
wherein the chemical solution comprises:
 - at least one zinc (Zn) ion source for providing a plurality of Zn ions;
 - at least one copper (Cu) ion source for providing a plurality of Cu ions;
 - at least one complexing agent for complexing the plurality of Cu ions;
 - at least one pH adjuster; and
 - at least one wetting agent for stabilizing the chemical solution, all being dissolved in a volume of deionized (DI) water.

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13. A device, as recited in Claim 11,
wherein the at least one zinc (Zn) ion source comprises at least one zinc salt
selected from a group consisting essentially of zinc acetate ((CH₃CO₂)₂Zn),
zinc bromide (ZnBr₂), zinc carbonate hydroxide (ZnCO₃·2Zn(OH)₂), zinc
dichloride (ZnCl₂), zinc citrate ((O₂CCH₂C(OH)(CO₂)CH₂CO₂)₂Zn₃), zinc
iodide (ZnI₂), zinc L-lactate ((CH₃CH(OH)CO₂)₂Zn), zinc nitrate
(Zn(NO₃)₂), zinc stearate ((CH₃(CH₂)₁₆CO₂)₂Zn), zinc sulfate (ZnSO₄), zinc
sulfide (ZnS), zinc sulfite (ZnSO₃), and their hydrates.

14. A device, as recited in Claim 11,
wherein the chemical solution further comprises at least one complexing agent for
complexing the plurality of Zn ions being dissolved in the volume of DI water,
wherein the at least one complexing agent for complexing the plurality of Zn ions
comprises tartaric acid (HO₂CCH(OH)CH(OH)CO₂H), and
wherein the tartaric acid prevents precipitation of the plurality of Zn ions from the
chemical solution.

15. A device, as recited in Claim 11,
wherein the at least one copper (Cu) ion source comprises at least one copper salt
selected from a group consisting essentially of copper(I) acetate
(CH₃CO₂Cu), copper(II) acetate ((CH₃CO₂)₂Cu), copper(I) bromide (CuBr),
copper(II) bromide (CuBr₂), copper(II) hydroxide (Cu(OH)₂), copper(II)
hydroxide phosphate (Cu₂(OH)PO₄), copper(I) iodide (CuI), copper(II)
nitrate hydrate ((CuNO₃)₂), copper(II) sulfate (CuSO₄), copper(I) sulfide
(Cu₂S), copper(II) sulfide (CuS), copper(II) tartrate ((CH(OH)CO₂)₂Cu), and
their hydrates.

16. A device, as recited in Claim 11,
wherein the at least one complexing agent for the plurality of Cu ions comprises at
least one species selected from a group consisting essentially of ethylene
diamine “EDA” (H₂NCH₂CH₂NH₂) and ethylenediaminetetraacetic acid
“EDTA” ((HO₂CCH₂)₂NCH₂CH₂N(CH₂CO₂H)₂), and

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wherein the at least one compelling agent for the plurality of Cu ions prevents precipitation of the plurality of Cu ions from the chemical solution.

17. A device, as recited in Claim 11,
10 wherein the at least one pH adjuster comprises at least one pH-adjusting compound selected from a group of consisting essentially of ammonium hydroxide (NH_4OH) and tetramethylammonium hydroxide “TMAH” ($(\text{CH}_3)_4\text{NOH}$).
18. A device, as recited in Claim 11,
wherein the at least one wetting agent comprises a surfactant, and
wherein the surfactant comprises at least one surfactant selected from a group of surfactants consisting essentially of RE-610™ and polyethylene glycol (PEG).
19. A device, as recited in Claim 11,
wherein the Cu surface is formed by a process selected from a group consisting essentially of chemical vapor deposition (CVD), plasma vapor deposition (PVD), plasma enhanced chemical vapor deposition (PECVD),
5 electroplating, and electroless plating,
wherein said solvent comprises water, and
wherein said gaseous flow comprises gaseous nitrogen (GN_2).
20. A semiconductor device, having a copper-zinc alloy (Cu-Zn) thin film formed on a copper (Cu) surface by electroplating the Cu surface in a chemical solution,
comprising:
5 a semiconductor substrate having at least one Cu surface formed thereon; and
a Cu-Zn alloy thin film formed and disposed on the at least one Cu surface.